

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	1.8303	1.6265	N/A
RT2	12.6034	5.3085	N/A
RT3	16.0846	595.9000 m	N/A
RT4	50.4817	2.4691	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	350.7575 u	10.1757 m	N/A
CT2	9.1612 m	2.4412 m	N/A
CT3	112.4963 m	140.9460 m	N/A
CT4	1.3838	256.2536 u	N/A

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	3.3897	3.2051	N/A
RF2	14.1256	5.5968	N/A
RF3	15.0952	731.1845 m	N/A
RF4	48.3895	466.9155 m	N/A
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	1.2550 m	235.3452 u	N/A
CF2	9.1869 m	1.9043 m	N/A
CF3	107.7674 m	224.4059 u	N/A
CF4	1.2668	121.1269 m	N/A

Note: NA indicates not applicable

## Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

